

In the Claims

CLAIMS

Claims 1-68 (Canceled).

69. (Previously presented) A semiconductor construction comprising:

a semiconductor substrate having a trench extending partially therein and upper surfaces adjacent the trench;

an oxide layer formed over the upper surfaces of the semiconductor substrate and having an uppermost surface; and

an insulative material filling the trench and having a portion outward of the trench and semiconductor substrate, the portion comprising an outermost upper surface elevationally above the uppermost surface of the oxide layer, the portion further comprising sidewalls connecting the outermost upper surface with the oxide layer, the sidewalls comprising first and second curved segments, the first curved segment extending from the outermost upper surface and comprising a first apex directed away from the semiconductor substrate, and the second curved segment extending from the first curved segment to the oxide layer and comprising a second apex directed toward the semiconductor substrate, the second apex being elevationally at or above the uppermost surface of the oxide layer, an entirety of the insulative material comprising the same stoichiometry;

a polysilicon layer formed against the uppermost surface of the oxide layer and against the portion of the insulative material.

70. (Previously presented) The semiconductor construction of claim 69 wherein the insulative material comprises oxide.

71. (Previously presented) The semiconductor construction of claim 69 wherein the insulative material comprises a first insulative material partially filling the trench and a second insulative material formed over the first insulative material.

Claim 72 (Canceled).

73. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the first curved segments of the portion are elevationally above and between the sidewalls of the trench.

74. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the first curved segments of the portion are directly over the bottom wall of the trench.

75. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls intersecting the upper surfaces of the semiconductor substrate, the intersection being positioned elevationally directly below the second curved segment of the portion of the insulative material.

76. (Currently amended) The semiconductor construction of claim 69 wherein the trench comprises sidewalls extending substantially 90° perpendicular relative the upper surfaces of the semiconductor substrate.

77. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the sidewalls form right angles with the bottom wall.

78. (New) The semiconductor construction of claim 69 wherein the polysilicon layer directly contacts the sidewalls of the portion of the insulative material.

79. (New) The semiconductor construction of claim 69 wherein the polysilicon layer directly contacts the sidewalls and the outermost upper surface of the portion of the insulative material.